

SILICON TRANSISTORS

2SD1615, 2SD1615A

NPN SILICON EPITAXIAL TRANSISTORS POWER MINI MOLD

DESCRIPTION

2SD1615, 1615A are designed for audio frequency power amplifier and switching application, especially in Hybrid ntegrated Circuits.

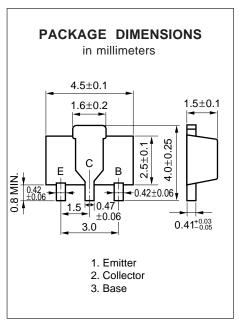
FEATURES

- · World Standard Miniature Package
- Low Vce (sat) Vce(sat) = 0.15 V
- · Complement to 2SB1115, 2SD1115A

ABSOLUTE MAXIMUM RATINGS

Maximum Voltages and Currents ($T_A = 1$	25°C)	2SD1615	2SD1615A	
Collector to Base Voltage	Vсво	60	120	V
Collector to Emitter Voltage	Vceo	50	60	V
Emitter to Base Voltage	Vево		6	V
Collector Current (DC)	Ic		1	Α
Collector Current (Pulse)*	Ic		2	Α
Maximum Power Dissipation				
Total Power Dissipation				
at 25°C Ambient Temperature**	Рт	2	2.0	W
Maximum Temperatures				
Junction Temperature	T_{j}	1	50	°C
Storage Temperature Range	Tstg	-55 to	+150	°C
	_			

^{*} PW \leq 10 ms, Duty Cycle \leq 50%



ELECTRICAL CHARACTERISTICS (TA = 25°C)

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS	
Collector Cutoff Current	Ісво			100	nA	2SD1615	Vcb = 60 V, IE = 0
				100	nA	2SD1615A	VcB = 120 V, IE = 0
Emitter Cutoff Current	I EBO			100	nA	$V_{EB} = 6.0 \text{ V}, I_{C} = 0$	
DC Current Gain	hFE1***	135	290	600		2SC1615	VcE = 2.0 V, Ic = 100 mA
		135		400		2SD1615A	
DC Current Gain	hFE2***	81	270			$V_{CE} = 2.0 \text{ V}, I_{C} = 1.0 \text{ A}$	
Collector Saturation Voltage	VcE(sat)***		0.15	0.3	V	Ic = 1.0 A, IB = 50 mA	
Base Saturation Voltage	V _{BE(sat)} ***		0.9	1.2	V	Ic = 1.0 A, I _B = 50 mA	
Base to Emitter Voltage	VBE***	600		700	mV	$V_{CE} = 2.0 \text{ V}, I_{C} = 50 \text{ mA}$	
Gain Bandwidth Product	f⊤	80	160		MHz	VcE = 2.0 V, IE = -100 mA	
Output Capacitance	Соь		19		pF	Vcb = 10 V, IE = 0, f = 1.0 MHz	

^{***} Pulsed: PW \leq 350 μ s, Duty Cycle \leq 2 %

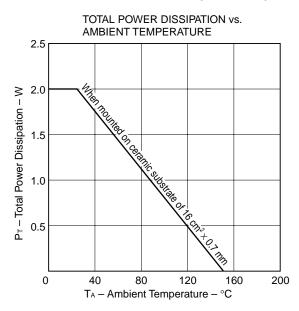
hre Classification

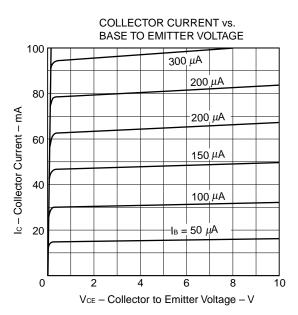
MARKING	2SD1615	GM	GL	GK
	2SD1615A	GQ	GP	
h	E	135 to 270	200 to 400	300 to 600

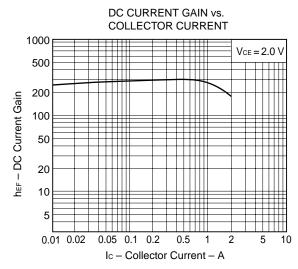
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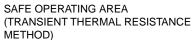
^{**} When mounted on ceramic substrate of 16 cm $^2 \times 0.7$ mm

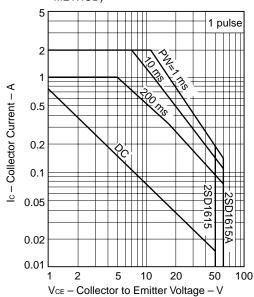
TYPICAL CHARACTERISTICS (T_A = 25°C)



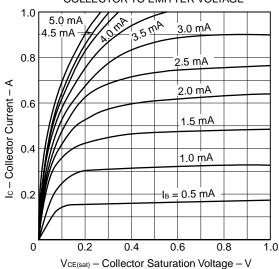




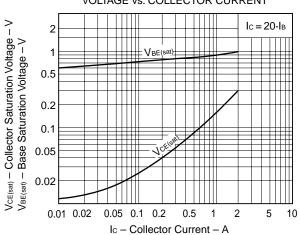


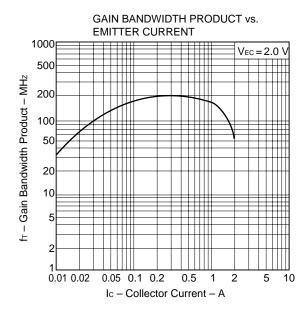


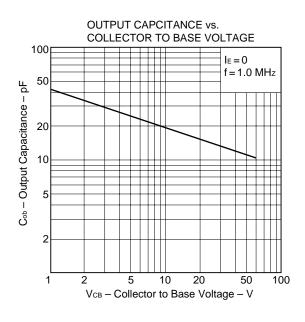
COLLECTOR CURRENT vs. COLLECTOR TO EMITTER VOLTAGE

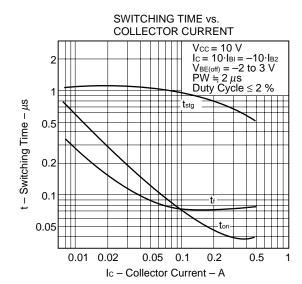


COLLECTOR AND BASE SATURATION VOLTAGE vs. COLLECTOR CURRENT











[MEMO]

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